

### Non-Ionising Energy Loss (NIEL) Calculation Software and Verification

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P.G. Rancoita, ESTEC 7 March, 2017



### Second Year Tasks (kick-off date Dec 16, 2015: from Dec 17. 2016 $\rightarrow$ 16 Dec. 2017)

Task 4: NIEL Data Analyses, Model and Software Framework Updates, Recommendations (2<sup>nd</sup> year) Task 5: Maintenance (2<sup>nd</sup> year) (Univ. and INFN Milano-Bicocca)



Task 3: DLTS measurements of Irradiated Test Samples (2<sup>nd</sup> year) (Univ. and INFN Milano-Bicocca, IMEN-CNR, CESI)











### **SR-NIEL**

### Displacement Damage and NIEL



SR

NIEL

**Non-Ionizing Energy Loss:** 

$$NIEL(E) = N \int_{T_d}^{T_{max}} TL(T) \frac{d\sigma(T, E)}{dT} dT$$

Frenkel-pairs:

$$FP \approx \frac{E_{dis}}{2.5T_d}$$

**Energy density** which goes into **displacement** [MeV/cm<sup>3</sup>]:

Displacement threshold energy

$$E_{dis} = \int_{E_{min}}^{E_{max}} NIEL(E)\Phi(E)dE$$
  
Minimum incoming energy  
to generate displacement

 $\Phi(E)$ :Spectral Fluence  $[\text{cm}^{-2}]$ N:Number of Target Atoms  $[\text{cm}^{-3}]$ T:Target kinetic EnergyL(T):Lindhard's partition function

 $\frac{d\sigma(T,E)}{dT}$  differential cross section 4

#### NIEL Proton or nucleus Coulomb Cross Section SR on nuclei (>about 50 keV/nucl)

It is based on the relativistic extension to jon-jon screened Coulomb scattering of the Wentzel-Moliere treatment - already used for electron and muon scattering in Geant4 –

$$\frac{d\sigma(\theta)}{d\Omega} = \left(\frac{Z_1 Z_2 e^2}{pc\beta}\right)^2 \frac{1}{\left(2A_s + 1 - \cos\theta\right)^2}$$

are the rest masses of the two particl  $m_1, m_2$ is the invariant mass  $M_{12}$ 







If  $Z_1 = 1$  $a_{TF} = \frac{0.88534a_0}{0.88534a_0}$ 

st masses of the two particles 
$$A_s = \frac{1}{4} \left( \frac{1}{pa_{TF,un}} \right) \left[ \frac{1.13 + 3.76}{\beta} \right]$$
  
and with screening lengths as in ICRU-49 (1993)

for incident particle If  $Z_1 > 1$ 

$$a_{un} = \frac{0.88534a_0}{\left(Z_1^{.23} + Z_2^{.23}\right)}$$

References:

C. Leroy and P.G. Rancoita (2016), Principles of Radiation Interaction in Matter and Detection - 4th Edition -, World Scientific (Singapore), Sects. 2.2-2.2.2 (from 2<sup>nd</sup> edition)

M.J. Boschini et al. "Nuclear and Non-Ionizing Energy-Loss for Coulomb

Scattered Particles from Low Energy up to Relativistic Regime in Space Radiation Environment." Proc. of the 12° ICATPP, Como 7-8/10/2010), World Scientific (Singapore) 2011, 9-23

Below 50 keV, use ZBL screened universal potential approach as from ICRU 1993 (protons and alphas)

# ZBL Approximation (lower than about 50 keV/nucl)

Approximation of the Ziegler, Biersack and Littmark (ZBL) screened potential



The function f(x) comes from the fit (with 4 coefficients) of the nuclear stopping power as function of the universal reduced energy  $\varepsilon$ 



Collision parameter

ZBL universal reduced energy

and with screening lengths as in ICRU-49 (1993)

for incident particle

If  $Z_1 > 1$ 

$$a_{un} = \frac{0.88534a_0}{\left(Z_1^{.23} + Z_2^{.23}\right)}$$

#### References:

S. R. Messenger et. al, "NIEL for Heavy Ions: An Analytical Approach", IEEE Transaction on Nuclear Science, V 50, N 6 (2003)

lf *Z*<sup>1</sup> =1

 $a_{TF} = -$ 

 $0.88534a_0$ 

S. R. Messenger et. al, "The Simulation of Damage Tracks in Silicon", IEEE Transaction on Nuclear Science, V 51, N 5 (2004)



#### References:

C. Leroy and P.G. Rancoita (2016), Principles of Radiation Interaction in Matter and Detection - 4th Edition -, World Scientific (Singapore), Sects. 2.4-2.4.3

M.J. Boschini et al "An Expression for the Mott cross section of electrons and positrons on nuclei with Z up to 118" Radiat. Phys. Chem. (2013), http://dx.doi.org/10.1016/j.radphyschem.2013.04.020

M.J. Boschini et al."Nuclear and Non-Ionizing Energy-Loss of Electrons with low and Relativistic Energies in Materials and Space Environment" Proc. Of the 13th ICATPP (13th ICATPP, Como 3-7/10/2011).

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### SR (Screened Relativistic) –NIEL Treatment Summary

- sr-treatement (for nuclear stopping power and NIEL) regards the interactions on screened nuclear potentials from protons, ions and electrons at low and relativistic energies,
- for any ELEMENT or COMPOUND (by means of BRAGG's RULE up to 10 elements)
- It accounts for nuclear form factors (in case of electron scattering).
- It includes both Norgett-Robinson-Torrens (1975) and Akkerman and Barak (2006) partition functions
- It provives NID doses for spectral particle fluences (as suggested by users)
- the hadronic contributions (embedded from version 1.5) to overall NIEL are obtained from literature (when available):

a) for incoming protons up to 1 GeV; Insoo Jun, Michael A. Xapsos, Scott R. Messenger, Edward A. Burke, Robert J. Walters, Geoff P. Summers, and Thomas Jordan, Proton Non-ionizing Energy Loss (NIEL) for Device Applications, IEEE TRANSACTIONS ON NUCLEAR SCIENCE, VOL. 50, NO. 6, DECEMBER 2003, 1924-1928; the hadronic contribution for energies from 1 up to 24 GeV in Si absorber was obtatined from M. Huhtinen, Nucl. Instr. and Meth. A 491 (2002), 194-215.

b) for incoming alpha-particles up to 1 GeV/nucl; Insoo Jun, Michael A. Xapsos, and Edward A. Burke, Alpha Particle Nonionizing Energy Loss (NIEL), IEEE TRANSACTIONS ON NUCLEAR SCIENCE, VOL. 51, NO. 6, DECEMBER 2004, 3207-3210



Within *sr-niel framework*, damage functions (thus, NIEL values) for neutrons are also available:

- those derived from ASTM E-722 09 and 14 for Si and GaAs from version 2.1
- Currently, available computations for many elements based on NJOY 2012 (from Los Alamos) as INFN-ENEA collaboration within ASIF framework; planned an updated based on NJOY 2012 (updated version) and NJOY 2016

In addition, in sr-niel website users can find the electronic stopping power (and, thus, estimated TID doses).

- From version 2.6, Protons and ions on single elemental absorbers and compounds (obtained both by means of Bragg's rule and corresponding coumpond corrections, when available).
- Their values are obtatined using the "SRIM Module.exe" from SRIM 2013 code.
- From version 2.7, electrons on elemental absorbers and compounds obtained by polynomial (at 15<sup>th</sup> degree) fit capable to reproduce the NIST –ESTAR tables based on ICRU Report 37 with a maximum discrepancy < 1%.</li>



### Code for NIEL Calculation

SR-NIEL: Screened Relativistic (SR) Treatment of the Displacement Damage

SR NIEL	Screened Relativistic (SR) Nuclear Stopping Power Calculator (version 3.6.0)	Burna Para (P)
Home SR-NIEL Handbook	Bibliography News History and Citation Who in AMS02 MiB AMS02 MiB Guest	Book Login
You are here: Home		
Website Search	Screened Relativistic (SR) Treatment for Calculating the Displacement Damage and Nuclear Stopping Powers in Materials	Statistics Articles View Hits 121382
Main Menu: SR-NIEL Long Write Up • Home	SR-NIEL and Nuclear Stopping Power Calculators for Elements and Compounds (for instance, semiconductors)	
NIEL and displacement stopping     power	Website latest update on February 17, 2017	News
<ul> <li>Energy partition functions</li> <li>Nuclear stopping power for electrons, protons, ions</li> <li>Energetic nuclear recoil</li> <li>Screened relativistic treatment</li> <li>NIEL doese in GAAs solar cells</li> </ul>	Welcome to the SR-NIEL Calculator Website. In these pages you can find information about the Screened Relativistic (SR) Calculator of the Non-Ionizing Energy Loss of electrons, protons and ions passing through an absorber, generating displacement damages and, in case of semiconductors, introducing deep levels resulting from the Frenkel pairs created. NIEL doses are also provided.	Hadronic contribution revised Read more
<ul> <li>GaAs NIEL tables for electrons and protons</li> <li>Neutron damage function, NIEL and hardness parameter</li> </ul>	Furthermore a calculator for the nuclear stopping powers of electrons, protons, light- and heavy-ions is available. The calculations are carried out based on the screened relativistic treatment for (elastic) Coulomb interactions on nuclei from low up to ultra relativistic energies.	SR-NIEL for Geant4 10.3 Read more
<ul> <li>Summary of neutron damage function, NIEL and hardness parameter</li> </ul>	In the present website version, a calculator for the probability of generating energetic recoil nuclei is also available. From version 1.5.2, additionally, the estimates of recoil energy	Update on Hadronic NIEL
Neutron spectral fluence     Hardness parameter and     1MeV neutron equivalent     NEL and minority contrary	fractions deposited via ionizing and non-ionizing processes are accessible using two of the mostly employed analytical approximations of energy partition function. From version 2.0 the electronic stopping power and ionizing dose calculator are also available.	Additional nuclei in NJOY based calculators
NEL and minority carrier     lifetime     Displacement damage and     min degradation of B IT	From version 2.1 the current calculator allows one to obains NIEL values and NIEL doses for neutrons in Si and GaAs absorbers, derived from ASTM-722-09 and ASTM-722-14 standards	Read more
<ul> <li>NIEL dose calculation for neutron using Robinson and Akkerman partition functions</li> </ul>	From version 3.0 registered users can access to SR-NIEL web calculators with additionally implemented Akkerman and Barak (2006) partition function; For information please contact info@scniel.org	contribution to NIEL of alpha particle
Comparison of Damage     Eurocions obtained with	Currently, additional functionalities implemented into NIEL calculators for registered users are:	Read more
Akkerman and Robinson	electron NIEL with Akkerman partition function;	NIEL Dose Calculator using

On line Calculators available at: www.sr-niel.org

This is a **C++** analytical code and has been developed to calculate the Non Ionizing Energy Loss of electrons, protons and ions with the possibility to <u>change the displacement</u> <u>threshold energy</u>

Moreover is possible to select different **nuclear form factor** for electrons and switch on/off the **hadronic contribution** for protons

The site is continuously updated (now version 3.6.0)



Projectile

semiconductor based) Devices.

As basic sr-niel reference: C. Leroy and P.G. Rancoita (2016), Principles of Radiation Interaction in Matter and Detection - 4th Edition -, World Scientific (Singapore), pages 1344.



### **Brief Version History**

#### www.sr-niel.org

NIEL calculator for **electrons**, **protons** & **ions** in any kind of target material (compound with Bragg rule)

added NIEL calculator for **neutrons** in **Si** and **GaAs** based on ASTM Standard damage functions (E722-09 and E722-14)

sr-niel handbook available srnielhandbook.altervista.org

availability of both Robinson and Akkerman partition functions

added NIEL calculator for **neutrons** in **C**, **N**, **Si**, **Ga**, **As** based on NJOY results (compound with Bragg rule)

calculators available for spectral fluences for electrons, protons, ions and neutrons; cross reference to handbook; hadronic contribution for alpha-particles etc.

Version 1.5.0 (Nov. 2014)

Version 2.7.1 (Feb 2016)

Version 2.8.0 (Feb 2016)

Version 3.0.0 (May 2016)

Version 3.2.0 (July 2016)

Version 3.6.0 Current version (February 2017) update no. 30



# SR-NIEL ESA Implementations

	Spenvis	GRAS	Mulassis	
SR-NIEL Version	1.5/2.8	2.8	2.8	
Status	NIEL Calculator (v 1.5, provided to ESA in 2014); implemented into public SPENVIS v. 4.6.8 in 2016 Intermediate v. 2.8 updated October 2016 on ESA servers; version 3.6 under implementation	Implementation Completed v 2.8 (May 2016); version 3.6 under implementation	v 2.8 made available but never implemented; version 3.6 under implementation	
To do	•Transfer to public SPENVIS version (tbd with ESA); under discussion	•Transfer to official GRAS version (tbd by ESA), under discussion	•Transfer to official Mulassis version (tbd by ESA), under discussion	





### Initial Geant4 Implementation

The scattering calculations we developed, are included in Geant4 and in 2 different physic class:

Since Geant4 version 9.4 (February 2011)

- G4IonCoulumbScatteringModel
- G4IonCoulumbCrossSection



For Protons and Ions Coulomb scattering and for E > 50 keV/nucl

#### Since Geant4 version 9.5 (October 2012)

- G4eSingleCoulumbScatteringModel
- G4ScreeningMottCrossSection

Electrons Coulomb scattering with *Exponential nuclear form factor* 

NIEL calculation is included in the external example test58





### Geant4 Implementation

#### Accomplished by IV quarter 2016 / I quarter 2017:

•The classes were updated to match Geant4 v 10.3 (Dec 2016)

•Full Mott cross-section for electron interaction up to Z=92, based on M.J.

Boschini et al., (2013) (An expression for the Mott cross section of electrons and positrons on nuclei with Z up to 118, Rad. Phys. Chem. 90, 39-66.)

•Minor bugs where spotted and fixed

•Implement other form factors for electrons cross section (*Gaussian, Uniform nuclear form factors in addition to exponential*)

#### To be done

•Improve computing time of the electrons class

•Implement hadronic contribution for protons & alpha's (available via test 58)



### Exs. Geant4 FF implementation





# Institutes and Industries using calculators available at www.sr-niel.org



### Main Institute and Industries using calculators on www.sr-niel.org

The bulk of web-calculators were gradually posted online by May 2015 (v 1.5 in November 2014) At present (v. 3.6.0):

Total webpages accessed > 121,000 at the end of Feb 2017

Requested Calculations from external users: 5496 at end of Feb 2017 (4338 on October 17, 2016)

→ The following slides are based on 2813 requests calculations from Identified Laboratories or Industries

#### 40.3% from USA

Laboratories and Industries with > 50 webcalculator requests:

SANDIA National Laboratories EADS Deutschland GmbH Ohio State University CERN Cassidian-Optronics-GmbH Germany

ESA CNES Ohio State University University of Louisiana at Lafayette

### Europe I

#### **ITALY**

- ESA (ESRIN) ٠
- **ENEA**
- INFN ٠
- **Fondazione Bruno Kessler** ٠
- LNL Laboratori Nazionali di Legnaro
- Università degli studi di Cassino ٠
- Università di Trieste ٠
- Fondazione San Raffaele del Monte Tabor ٠
- Ente per le Nuove Tecnologie, Energia ed Ambiente ٠
- **ENEA C.R. Frascati** ٠
- INAF ٠
- Oss. Astronomico di Collurania Teramo ٠

2004

#### **SPAIN**

- Instituto Nacional de Tecnica Aeroespacial ٠
- Universidad de Sevilla ٠
- Instituto Nacional de Tecnica Aeroespacial ٠
- Universidad de Oviedo ٠
- Universidad de Zaragoza ٠

#### **SWITZERLAND**

- CERN
- University of Bern
- **Paul Scherrer Institut**

MA C

#### **TURKEY**

- Yozgat Bozok Universitesi ٠
- Middle East Technical University(METU)

#### **HUNGARY**

**Budapest University of Technology and Economics** 

#### **GERMANY**

- EADS Deutschland GmbH
- **Cassidian-Optronics-GmbH**
- **DIEHL Informatik GmbH**
- **GWD** Goettingen
- **TSBS fuer EADS Deutschland GmbH**
- Fraunhofer GERMY
- **AZUR SPACE Solar Power GmbH**
- Johann Wolfgang Goethe-Universitaet Frankfurt
- **Ruprecht-Karls-Universitaet Heidelberg**
- GSI Helmholtzzentrum fuer Schwerionenforschung GmbH
- Universitaet der Bundeswehr Muenchen
- Max-Planck-Institut fuer Plasmaphysik
- **OHB System AG**
- Kabel Baden-Wuerttemburg GmbH
- Helmholtz-Zentrum Dresden-Rossendorf
- Friedrich Alexander Universitaet Erlangen-Nuernberg
- **Universitaet Leipzig**
- Lti DRIVES GmbH
- Jena-Optronik
- **Universitaet Kiel**

#### **NORWAY**

**University of Oslo** 

Bergen University, Norway

#### **AUSTRIA**

- **Austrian Academy of Sciences**
- **Technische Universitat Wien**

#### **GREECE**

•

- Aristotle University of Thessaloniki
- **BELGIUM** Universite Catholique de Louvain



National Institute for Physics and Nuclear Engineering Horia Hulubei

#### **CANADA**

- Atomic Energy of Canada Ltd
- Iridian Spectral Technologies Ltd
- Bell Canada
- TekSavvy Solutions, Inc.
- University of Winnipeg
- Nanowave Technologies Inc
- University of Victoria

#### ARGENTINA

• Fondation Innova T

#### BRASIL

• Universidade Estadual de Campinas

#### **USA**

- Solar Junction
- TRIDENT SPACE & DEFENSE
- Space Exploration Technologies Corporation (SPACEX)
- Los Alamos National Laboratory
- Mayo Foundation for Medical Education and Research
- Rochester Institute of Technology (RIT-3)
- United Technologies Research Center (UTRC)
- Texas A&M University (TAMU)
- Thomas Jefferson National Accelerator Facility
- Lockheed Martin Corporation

#### USA

America

- SANDIA National Laboratories
- Ohio State University
- University of Louisiana at Lafayette
- California Institute of Technology
- The Aerospace Corporation LA USA
- FERMILAB
- Teledyne Brown Engineering (TBE)
- University of California
- US Army 754th Electronic Systems Group (7ESG)
- Cal State Fullerton (CSUF)
- Northrop Grumman Corp. (NGC-1)
- General Dynamics Advanced Information Systems, Inc
- Johns Hopkins University Applied Physics Laboratory
- US Navy
- Oak Ridge National Laboratory (ORNL)
- Pacific Northwest National Laboratory (PNNL-Z)
- Raytheon Company (RAYTHE)
- NASA
- California State University
- University of Massachusetts Lowell
- Virginia Commonwealth University (VCU-Z)
- Lawrence Berkeley National Laboratory
- Lawrence Livermore National Laboratory (LLNL-1)
- Ball Corporation (BALLCO)
- Michigan State University
- The Boeing Company
- AHS-Hillcrest-Medical-Center
- Massachusetts Institute of Technology
- University of Alaska
- SLAC National Accelarator Laboratory
- Idaho National Laboratory (INL-12)
- Purdue University (PURDUE)
- Vanderbilt University (VANDER)

### Asia





### **Experimental Results**





### **Test Irradiation Campaign**

Protons Irradiation

**Electrons Irradiation** 

Energy [MeV]	Fluence [cm <sup>-2</sup> ]	Dose [MeV g <sup>-1</sup> ]	Dose [Gy]	Energy [MeV]	Fluence [cm <sup>-2</sup> ]	Dose [MeV g <sup>-1</sup> ]	Dose [Gy]
	1.70E+011	1.15E+10	0 1.85		1.00E+014	1.11E+09	0.18
0.7	3.30E+011	2.24E+10	3.59	1	5.00E+014	5.56E+09	0.89
	4.50E+011	3.05E+10	4.89		1.00E+015	1.11E+10	1.78
4	4.50E+010	2.23E+09	0.36	1.5	5.00E+014	1.00E+10	1.60
I	2.30E+011	1.14E+10	1.82		1.00E+015	2.00E+10	3.21
0	4.20E+011	1.12E+10	1.79	3	2.00E+014	7.48E+09	1.20
2	8.40E+011	2.23E+10	3.58		4.00E+014	1.50E+10	2.40

Irradiated at CSNSM Orsay (France)

Irradiated at Delft (The Netherlands)

Dose in calculated with SR-NIEL (v. 2.8) in GaAs (Ed=21eV, Robinson PF) as target material

### The radiation behaviour is very important for EOL performances estimation

- To deeply analyse the behaviour of CTJ30 solar cells after proton and electron irradiation, not only the triple junction but all subcell was irradiated and annealed following the schema below.
- For each conditions the following cells (2x2 cm2) were irradiated:

2  CT 120  In CaP/CaAa/Ca	I	Energy (MeV) (p/cm2)
- 3 CTJ30, INGAP/GAAS/Ge	proton	0.7 1.70E+11
- 3 TOP InGaP		0.7 3.30E+11
		0.7 4.50E+11
<ul> <li>3 MID (In)GaAs (with InGaP filter)</li> </ul>		1 4.50E+10
		1 2.30E+11
<ul> <li>3 Bottom Ge (with InGaP and InGaAs filter)</li> </ul>		2 4.20E+11
		2 8.40E+11
Solar cells were measured at CESI under solar		Fluences
		(e/cm2)
simulator dual source immediately after irradiation	electron	1 1.00E+14
2 out of three complex for each irrediction conditions		5.00E+14
2 out of three samples for each inadiation conditions		1.00E+15
and each solar cells type were annealed (8 hours		1.5 5.00E+14
		1.00E+15
under 1 sun, 60 °C)		3 2.00E+14
1 sample will be measured in three months to analyse		4.00E+14

self annealing

CESI SOL

Fluences



### Total irradiated samples

3J solar cells : 14 fluences x 3 samples = 42 samples 1J solar cells : 14 fluences x 3 types x 3 samples = 126 samples Diodes for DLTS: 14 fluences x 2 types x 2 samples = 56 samples x 25 diodes = 1400

Solar cells 2 cm x 2 cm Diodes 500 micron diameter (obtained with MESA technology) Total number of devices : 1568





#### Sample for DLTS measurements mounted on TO39 holder



Photograph of a top junction sample, 3.3x3.3 mm<sup>2</sup>, mounted on a TO-39 holder. The dots correspond to the AuGeNi top contacts (0.4 mm in diam). Two mesa diodes are connected to the isolated pins with gold wires. The back ohmic contact is soldered to the case by silver paste.

### 3J and 1J solar cells



### Self annealing: 4 weeks protons, 2.5 weeks electrons (after Irradiation)

### Annealing: in addition to self annealing, 8 hours under sun simulator, 60 °C

in all calculations, we used the stoichiometry (and layer thicknesses) from CESI

#### In this analysis the optimization is carried out accounting for, simultaneously, $P/P_{max}$ , $I_{sc}$ , $V_{oc}$ obtained from all irradiations of electrons and protons

#### NIEL doses are obtained from sr-niel as a function of E<sub>d</sub>

Used the standard semi-empirical expression with an additional constant term from C. Baur et al. (2005) 31 IEEE Photovoltaic Specialists Conference:

$$(1-par2)-par0 \cdot log_{10}(1+par1 \cdot Dose)$$

That reduce to the usual one if par2=0 (as found for for 3J, 1J Top, 1J Mid)

$$1 - \text{par0} \cdot \log_{10}(1 + \text{par1} \cdot \text{Dose})$$



#### GaAs NIEL with Ed=10 eV and Robinson partition function (self-annealing)



### 3J cells: Search for best Ed value for 10 < Ed < 30 eV





1J mid cells: Search for best Ed value for Ga and As for 10 < Ed < 30 eV



1J top cells: Fixed Ed = 21 for Ga and P Search for best Indium Ed value for 30 < Ed < 50 eV GaP (Ed=21 eV), In (Ed=40 eV) NIEL and Robinson partition function (self-annealing)



SR

NIEL

1J bottom cells: Search for best Ed value for 30 < Ed < 50 eV





### P/P<sub>max</sub> After Annealing

Protons Irradiation

**Electrons Irradiation** 

Energy [MeV]	Variation [%]	Energy [MeV]	Variation [%]
0.7	5.1 ± 1.6	1	3.2 ± 1.7
1	$2.4 \pm 0.5$	1.5	4.7 ± 0.4
2	3.7 ± 1.0	3	4.9 ± 1.0

### **DLTS Preliminary Results**



## DLTS spectra obtained on a middle junction irradiated with electrons (1 MeV at a fluence of 10<sup>15</sup> cm<sup>-2</sup>)

using different reverse voltage Vr at fixed pulse amplitude of 1.4 V.

Emission rate =46 s<sup>-1</sup>, pulse width=500 µs, V1=pulse voltage.





DLTS spectrum (Vr= -1.5 V) of a middle cell diode irradiated with protons (energy 0.7 MeV and fluence 4.5x10<sup>11</sup> cm<sup>-2</sup>) is compared to that of a middle cell diode irradiated with electrons (energy 1 MeV and fluence 1x10<sup>15</sup> cm<sup>-2</sup>). NIEL dose ratio (proton/electron) = 2.74





### Preliminary Remarks on DLTS

i) Three main DLTS peaks, from the top of the valence band labelled as E1 (0.21 eV), E2 (0.45 eV) and E3 (0.71 eV), and a broad low temperature shoulder of E2 are observed in both electron and proton irradiated samples.

ii) The E3 peak, that is mainly located at the p/n interface and is also present in the non-irradiated sample, has been associated to interface defects.

iii) E1, E2 (and related shoulder) have been attributed to irradiation induced defects since: i) they are uniformly distributed in the region of the depletion layer investigated by DLTS, ii) their density increases with absorbed dose and iii) they are not detected in non-irradiated samples



# Preliminary Remarks on Comparison between electron and proton irradiated samples

i) An additional DLTS peak at a temperature of about 365 K is observed for intermediate reverse voltage (Vr=-1.5 V) in the proton irradiated sample. Since this peak disappears for higher reverse voltage and is not observed in non-irradiated samples, it is attributed to defects induced by proton irradiation near the interface. These defects might be newly formed defects by the proton irradiation, or due to interaction between the proton irradiation and already present interface defects.

ii) The peak amplitude RATIO E2/E1 is observed to be larger for the proton irradiated sample than for the electron irradiated one

iii) While the NIEL dose ratio protons/electrons is 2.74, the ratio of the defect concentrations (protons/electrons) derived from E2 is slightly larger (3.4). The ratio of defect concentrations (protons/electrons) derived from E1, on the contrary, is slightly lower (about 2.2)



### Preliminary remarks (symmary) mostly regarding self-annealing data

- From a global fit on P/Pmax, Isc, Voc self annealing data for electrons and protons, Ed ≈ 21 eV for Ga and As (for 1J solar cells) is already reached after a few weeks (of self-annealing time). For 3J the effective Ed for Ga and As can be affected by modelling the 3J solar cell as a 1J GaAs cell.
- 10 eV displacement threshold energy is not appropriate for "GaAs based" solar cells.
- Doses are calculated using sr-niel (v. 3.6).
- the ratio protons/electrons of the peak amplitudes E2 (E1) is observed to be larger (smaller) with respect to NIEL Dose ratio (2.74)

Two abstracts submitted: To IEEE NSREC Displacement Damage dose and DLTS Analyses on Triple and Single Junction solar cells irradiated with electrons and protons, Carsten Baur5, Roberta Campesato1, Mariacristina Casale1, Massimo Gervasi 2,3, Enos Gombia 4, Erminio Greco1, Aldo Kingma4, P.G. Rancoita2, Davide Rozza2, Mauro Tacconi2,3 To IEEE PVSEC NIEL DOSE Analysis on Triple Junction cells 30% efficient and related single junctions, Roberta Campesato 1, Erminio Greco1, , Mariacristina Casale1, Massimo Gervasi 2,3,

P.G. Rancoita2, Davide Rozza2, Mauro Tacconi2,3, Enos Gombia 4, Aldo Kingma4, Carsten Baur5

### Back up









Capacitance vs frequency of a mesa structure obtained on the middle cell.



Determined based on overall rates of defects introduction using DLTS measurements

Data points from Pons et al, J. Appl. Phys. 51, 2038 (1980) for **electron irradiated GaAs** with **superimposed current NIEL calculations** with 10 and 25 eV *displacement threshold energy* **normalized to the highest energy point** 



the (self-) annealing effect is **expected to cause a shift of the damage energy threshold to a value larger than 10 eV**. In that paper, the authors correctly remarked about a possible disappearing of divacancies. (see C.Baur et al. (2014), NIEL dose dependence for solar cells irradiated with electrons and protons, Proc. of the 14th ICATPP, September 23--27 2013, Villa Olmo, Como, Italy, World Scientific, Singapore, 698-713; ISBN: 978-981-4603-15-7)





Correlatd sites II: <u>www.geomagsphere.org</u> under full revision





### Spenvis Implementation

<u>SPENVIS Project: TRY</u> Miscellaneous INFN Screened Relativistic Non-Ionising Energy Loss (SR-NIEL) Calculator

Incident Particle: Be				
Ion Model:	Hadron + Coulomb V			
Target Materials				
Target Material:	User defined			
# Elements:	2 •			
Target Material Z	Stoichiometric Index	Threshold Energy [eV]		
31:Ga 🔻	1	21		
33:As 🔻	1	21		
NIEL Energy ranges				
Minimum Energy:	1.0E-4 [MeV]			
Maximum Energy:	1000.0 [MeV]			
# of Energy steps:	150			

Screenshot of the SR-NIEL Calculator input mask in SPENVIS v. 4.6.8

Reset Run

Model developed by



SEZIONE DI MILANO-Bicocca